To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HSU276

Silicon Schottky Barrier Diode for Mixer

ADE-208-078F(Z)

Rev. 6
Jul. 1996

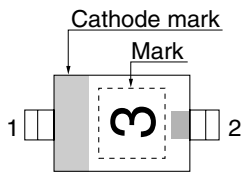
Features

- High forward current, Low capacitance.
- Ultra small Resin Package (URP) is suitablefor high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU276	3	URP

Pin Arrangement



1. Cathode
2. Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	3	V
Average rectified current	I_O	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	I_R = 1 mA
Reverse current	I_R	—	—	50	µA	V_R = 0.5V
Forward current	I_F	35	—	—	mA	V_F = 0.5V
Capacitance	C	—	—	0.85	pF	V_R = 0.5V, f = 1 MHz
ESD-Capability[*1]	—	30	—	—	V	C = 200pF , Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion ; $I_R \geq 100\mu A$ at V_R = 0.5 V

Main Characteristic

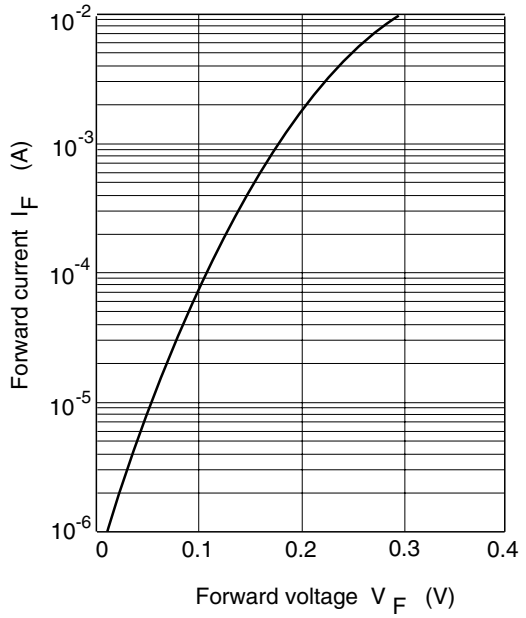


Fig.1 Forward current Vs. Forward voltage

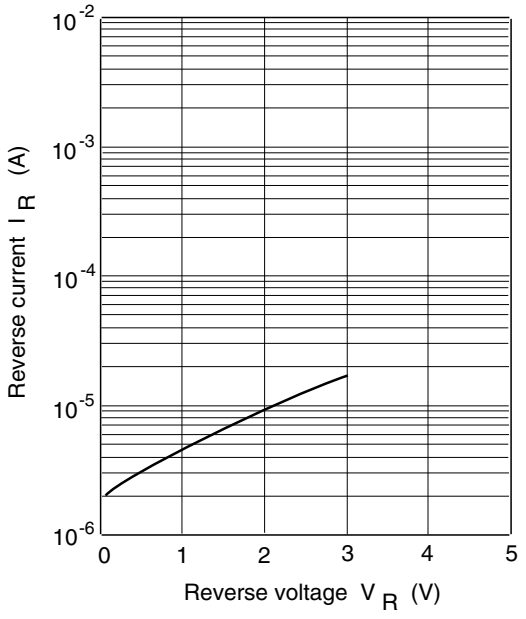


Fig.2 Reverse current Vs. Reverse voltage

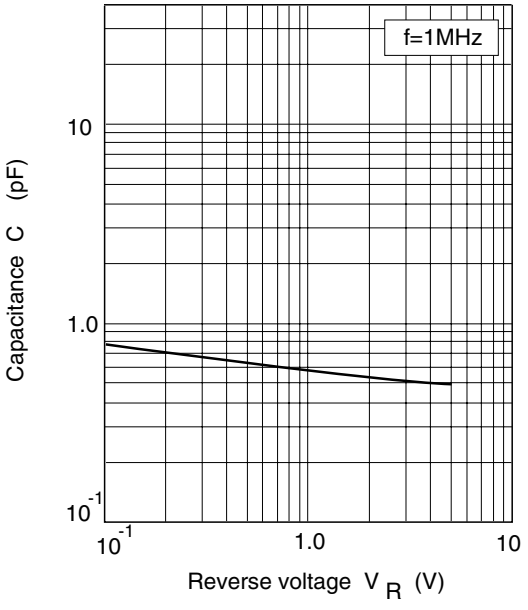
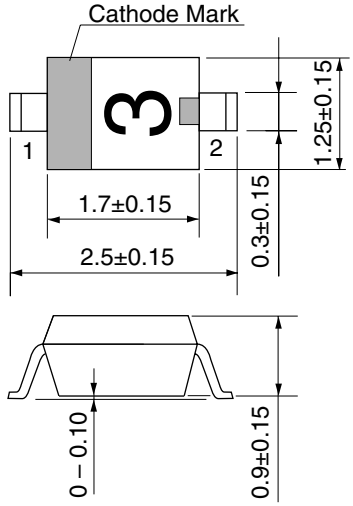


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit : mm



1. Cathode
2. Anode

Hitachi Code	URP
JEDECCode	—
EIAJCode	—
Weight(g)	0.004

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